



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

1758

11/14/02  
#7/Amend  
A

In re Application of

Hung Yip Ng

Serial No.: 09/821,478

Group Art Unit: 1756

Filed: March 29, 2001

Examiner: Sagar, Kripa

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TC 1700

For: METHOD FOR POLYSILICON CONDUCTOR (PC) TRIMMING FOR SHRINKING  
CRITICAL DIMENSION AND ISOLATED-NESTED OFFSET CORRECTION

Honorable Commissioner of Patents  
Washington, D.C. 20231

AMENDMENT UNDER 37 C.F.R. §1.111

Sir:

In response to the Office Action dated August 12, 2002, please amend the above-  
identified application as follows:

IN THE CLAIMS:

Please amend claims 1 and 8 to read as follows:

1. (Amended) A method of forming a semiconductor device, comprising:
- providing a structure having a first critical dimension;
- forming a lithographic pattern on said structure;
- etching said structure with an O<sub>2</sub>-containing material to trim said first critical dimension
- to a second critical dimension, said second critical dimension being smaller than said first critical dimension; and
- correcting an offset between a nested feature printed on said structure and an isolated

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